



3A ULTRA LOW DROPOUT LINEAR REGULATOR WITH ENABLE

Description

The AP7175 is a 3.0A ultra low-dropout (LDO) linear regulator that features an enable input and a power-good output.

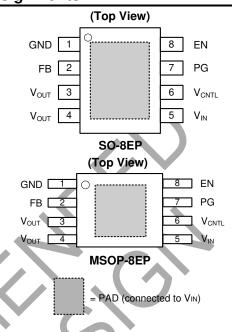
The enable input and power-good output allow users to configure power management solutions that can meet the sequencing requirements of FPGAs, DSPs, and other applications with different start-up and power-down requirements.

The AP7175 features two supply inputs, for power conversion supply and control. With the separation of the control and the power input very low dropout voltages can be reached and power dissipation is reduced.

A precision reference and feedback control deliver 1.5% accuracy over load, line, and operating temperature ranges.

The AP7175 is available in SO-8EP and MSOP-8EP package with an exposed PAD to reduce the junction to case resistance and extend the temperature range it can be used in.

Pin Assignments



Features

- V_{IN} Range: 1.2V to 3.65V V_{CNTL} 3.0V to 5.5V
- Adjustable output voltage
- Continuous Output Current I_{OUT} = 3A
- Fast transient response
- Power on reset monitoring on V_{CNTL} and V_{IN}
- Internal Softstart
- Stable with Low ESR MLCC Capacitors
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Applications

- Notebook
- P0
- Netbook
- Wireless Communication
- Server
- Motherboard
 - Dongle
- Front Side Bus VTT (1.2V/3.3A)

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

Typical Applications Circuit

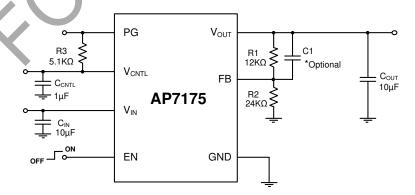


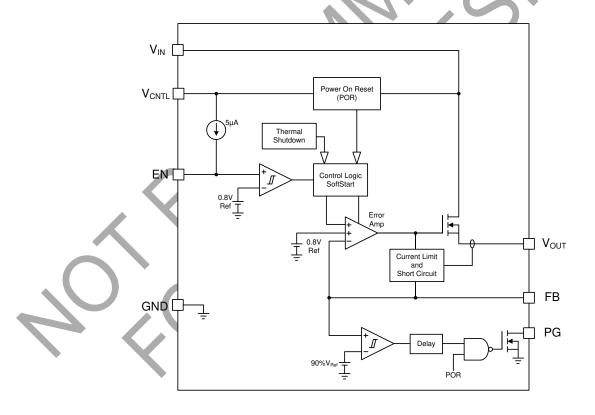
Figure 1. Typical Application Circuit



Pin Descriptions

Pin	Pin	Number	Frankling
Name	SO-8EP	MSOP-8EP	Function
GND	1	1	Ground
FB	2	2	Feedback to set the output voltage via an external resistor divider between V _{OUT} and GND.
V _{OUT}	3/4	3/4	Power Output Pin. Connect at least 10μF capacitor to this pin to improve transient response and required for stability. When the part is disabled the output is discharged via an internal pull-low MOSFET.
V _{IN}	5	5	Power Input Pin for current supply. Connect a decoupling capacitor (≥10µF) as close as possible to the pin for noise filtering.
V _{CNTL}	6	6	BIAS supply for the controller, recommended 5V. Connect a decoupling capacitor (≥1µF) as close as possible to the pin for noise filtering.
PG	7	7	Power Good output open drain to indicate the status of V_{OUT} via monitoring the FB pin. This pin is pulled low when the voltage is outside the limits, during thermal shutdown and if either V_{CNTL} or V_{IN} go below their thresholds.
EN	8	8	Enable pin. Driving this pin low will disable the part. When left floating an internal current source will pull this pin high and enable it.
PAD	EP	EP	Exposed pad connect this to V _{IN} for good thermal conductivity.

Functional Block Diagram



NOT RECOMMENDED FOR NEW DESIGN - NO ALTERNATE PART



AP7175

Absolute Maximum Ratings (Note 4) (@TA = +25°C, unless otherwise specified.)

Symbol	Parameter	Rating	Unit
V _{IN}	V _{IN} Supply Voltage (V _{IN} to GND)	-0.3 to +4.0	V
V _{CNTL}	V _{CNTL} Supply Voltage (V _{CNTL} to GND)	-0.3 to +7.0	V
V _{OUT}	V _{OUT} to GND Voltage	-0.3 to V _{IN} +0.3	V
_	PG to GND Voltage	-0.3 to +7.0	V
_	EN, FB to GND Voltage	-0.3 to V _{CNTL} +0.3	V
В	Power Dissipation (SO-8EP)	1.7	W
P_D	Power Dissipation (MSOP-8EP)	1.5	W
TJ	Maximum Junction Temperature	+150	°C
T _{STG}	Storage Temperature	-65 to +150	°C
T _{SDR}	Maximum Lead Soldering Temperature, 10 Seconds	+260	°C

Note:

Recommended Operating Conditions (@TA = +25°C, unless otherwise specified.)

Symbol	Param	neter	Min	Max	Unit
V _{CNTL}	V _{CNTL} Supply Voltage		3.0	5.5	V
V _{IN}	V _{IN} Supply Voltage		1.2	3.65	V
V _{OUT}	V _{OUT} Output Voltage (when V _{CNTL} -V	/ouτ >1.9V)	0.8	V _{IN} - V _{DROP}	V
I	V Output Current	Continuous Current	0	3	А
I _{OUT}	V _{OUT} Output Current	Peak Current	0	4	
	V _{OUT} Output Capacitance	I _{OUT} = 3A at 25% nominal V _{OUT}	8	1100	
Соит		I _{OUT} = 2A at 25% nominal V _{OUT}	8	1700	μF
		I _{OUT} = 1A at 25% nominal V _{OUT}	8	2400	
E _{SRCOUT}	ESR of Vout Output Capacitor		0	200	mΩ
T _A	Ambient Temperature		-40	+85	°C
TJ	Junction Temperature		-40	+125	°C

^{4.} Stresses greater than the 'Absolute Maximum Ratings' specified above, may cause permanent damage to the device. These are stress ratings only; functional operation of the device at these or any other conditions exceeding those indicated in this specification is not implied. Device reliability may be affected by exposure to absolute maximum rating conditions for extended periods of time.

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AP7175

Electrical Characteristics

 $(V_{CNTL} = 5V, V_{IN} = 1.8V, V_{OUT} = 1.2V \text{ and } T_A = -40 \text{ to } +85^{\circ}\text{C}, @T_A = +25^{\circ}\text{C}, unless otherwise specified.})$

Symbol Parameter Test Conditions Test Te								
North Vent Supply Current EN = Vent Iout = 0A	Symbol	Parameter	Test Conditions					
VCNTL VCNTL VCNTL Supply Current at Sundamon EN = CNTL Supply Current at EN = GND EN = GND Supply Current at Shutdown EN = GND E	,	OUDDENT		Min	Тур	Max		
Iso			EN V I OA	<u> </u>	1.0	1 5	m 1	
Shutdown	IVCNTL		EIN = V _{CNTL} , I _{OUT} =UA	_	1.0	1.5	IIIA	
POWER-ON-RESET (POR)	I _{SD}		EN = GND	_	15	30	μΑ	
Pising Vont POR Threshold Pising Vont POR Threshold Pising Vont POR Hysteresis Pising Vont Por	_	V _{IN} Supply Current at Shutdown	$EN = GND, V_{IN}=3.65V$			1	μΑ	
Voltr POR Hysteresis	POWER-0	ON-RESET (POR)						
Rising V _N POR Threshold	_	Rising V _{CNTL} POR Threshold	_	2.5	2.7	2.95	V	
No Port Nysteresis	_	V _{CNTL} POR Hysteresis	_		0.4	_	V	
Output Voltage FB = Vour	_	Rising V _{IN} POR Threshold	_	0.8	0.9	1.0	V	
Page	_	V _{IN} POR Hysteresis	_	1	0.5	_	V	
Output Voltage Accuracy	OUTPUT	· ·						
VREF Load Regulation Iour = 0.0 to 3A − 0.06 0.25 % Line Regulation Iour = 0.0 to 3A − 0.06 0.25 % Vour Pull-low Resistance Vour = 0.8V − 10 − 100 nA PORPOUT VOLTAGE Voin-to-Vour Dropout Voltage (Note 5) Voin-to-Vour Dropout Voltage (Note 5) Voin-to-Vour Dropout Voltage (Note 5) Voint- 1.8V (Note 5) T_J = 40 to +125°C − 0.26 0.31 − 0.26 0.23 0.28 − 0.26 0.31 − 0.26 0.31 − 0.26 0.23 0.28 − 0.26 0.31 − 0.26 0.23 0.28 − 0.26 0.31 − 0.26 0.31 − 0.26 0.23 0.28 − 0.26 0.23 0.28 − 0.26 0.23 0.28 − 0.26 0.31 − 0.26 0.31 − 0.26 0.23 0.28 − 0.26 0.31 − 0.26 0.23 0.28 − 0.26 0.31 − 0.26 0.23 0.28 − 0.26 − 0.26 0.28 − 0.26 − 0.26 − 0.26 </td <td></td> <td>Reference Voltage</td> <td>FB = V_{OUT}</td> <td></td> <td>0.8</td> <td></td> <td>V</td>		Reference Voltage	FB = V _{OUT}		0.8		V	
Value Load Regulation Lout = 0.4 to 3.4		Output Voltage Accuracy		-1.5	A	+1.5	%	
Line Regulation LouT = 10mA, VCNTL = 3.0, to 5.5 V -0.15	VREE	Load Regulation		1-1	0.06	0.25	%	
Vour Pull-low Resistance Vont = 3.3V, Ven = 0V, Vour > 0.8V	- 11121	Line Regulation		-0.15	_	+0.15	%/V	
Variable		V _{OUT} Pull-low Resistance		7	10	_	Ω	
VDROP Vonto-Vour Dropout Voltage (Note 5) Vont = 5.0V, lour = 3.0V, lour = 1.8V T _J = -40 to +125°C — 0.24 0.29 0.24 0.29 0.29 Vont = 0.00 Vout = 1.8V (Note 5) T _J = -40 to +125°C — 0.24 0.29 0.24 0.29 Volum = 1.8V (Note 5) T _J = -40 to +125°C — 0.24 0.29 0.20 0.28 0.28 0.28 0.29 Volum = 1.2V (Note 5) T _J = -40 to +125°C — 0.23 0.28 0.28 A <th< td=""><td></td><td>FB Input Current</td><td>V_{FB} = 0.8V</td><td>-100</td><td>_</td><td>100</td><td>nA</td></th<>		FB Input Current	V _{FB} = 0.8V	-100	_	100	nA	
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VDROP Vin-to-Vout Dropout Voltage (Note 5) Vont = 5.0V, lour = 3.0 Vont = 1.8V lour = 1.2V lour =			$T_{J} = +25^{\circ}C$	_	0.26	0.31		
Voron			$T_{\rm J} = -40 \text{ to } +125^{\circ}\text{C}$	_	_	0.42		
Indicates Ind	Vonon	V _{IN} -to-V _{OUT} Dropout Voltage	101/12	_	0.24	0.29	V	
LILIM Current-Limit Level T_j = -40 to +125°C	V DROP	(Note 5)	$I_{OUT} = 3A$ $T_{J} = -40 \text{ to } +125^{\circ}\text{C}$	_	_	0.40	v	
T _J = -40 to +125°C			Vour = 1 2V	_	0.23	0.28		
T _J = -40 to +125°C			$I_{\rm J} = -40 \text{ to } +125^{\circ}\text{C}$	_	_			
T _J = -40 to +125°C 4.2 — — A PROTECTIONS I _{SHORT} Short Current-Limit Level V _{FB} < 0.2V	Lim	Current-Limit Level			5.7	6.7	Α	
Short Current-Limit Level VFB < 0.2V			$T_J = -40 \text{ to } +125^{\circ}\text{C}$		_	_	Α	
T _{SD} Thermal Shutdown Temperature T _J rising — +170 — °C — Thermal Shutdown Hysteresis — +50 — °C ENABLE AND SOFT-START — EN Logic High Threshold Voltage V _{EN} rising 0.5 0.8 1.1 V — EN Hysteresis — 0.1 — V — EN Pull-High Current EN = GND — 5 — μA t _{SS} Soft-Start Interval — 0.3 0.6 1.2 ms — Turn On Delay From being enabled to Vout rising 10% 200 350 500 μs POWER-GOOD AND DELAY V _{THPG} Rising PG Threshold Voltage V _{FB} rising 90 92 95 % — PG Threshold Hysteresis — — 8 — % — PG Pull-low Voltage PG sinks 5mA — 0.25 0.4 V — PG Debounce Interval				Π				
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— EN Hysteresis — 0.1 — V EN Pull-High Current EN = GND — 5 — μA t _{SS} Soft-Start Interval — 0.3 0.6 1.2 ms — Turn On Delay From being enabled to V _{OUT} rising 10% 200 350 500 μs POWER-GOOD AND DELAY V _{THPG} Rising PG Threshold Voltage V _{FB} rising 90 92 95 % — PG Threshold Hysteresis — 8 — % — PG Pull-low Voltage PG sinks 5mA — 0.25 0.4 V — PG Debounce Interval V _{FB} < falling PG voltage threshold	ENABLE		Ly	0.5				
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t _{SS} Soft-Start Interval — 0.3 0.6 1.2 ms — Turn On Delay From being enabled to V _{OUT} rising 10% 200 350 500 μs POWER-GOOD AND DELAY V _{THPG} Rising PG Threshold Voltage V _{FB} rising 90 92 95 % — PG Threshold Hysteresis — 8 — % — PG Pull-low Voltage PG sinks 5mA — 0.25 0.4 V — PG Debounce Interval V _{FB} < falling PG voltage threshold			EN - GND					
— Turn On Delay From being enabled to V _{OUT} rising 10% 200 350 500 μs POWER-GOOD AND DELAY V _{THPG} Rising PG Threshold Voltage V _{FB} rising 90 92 95 % — PG Threshold Hysteresis — 8 — % — PG Pull-low Voltage PG sinks 5mA — 0.25 0.4 V — PG Debounce Interval V _{FB} < falling PG voltage threshold	tec			0.3		12		
POWER-GOOD AND DELAY V _{THPG} Rising PG Threshold Voltage V _{FB} rising 90 92 95 % — PG Threshold Hysteresis — 8 — % — PG Pull-low Voltage PG sinks 5mA — 0.25 0.4 V — PG Debounce Interval V _{FB} < falling PG voltage threshold	- 35		From being enabled to Vour rising 10%					
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— PG Pull-low Voltage PG sinks 5mA — 0.25 0.4 V — PG Debounce Interval V _{FB} < falling PG voltage threshold		·	V _{FB} rising	90	92	95	%	
— PG Debounce Interval V _{FB} < falling PG voltage threshold	_	PG Threshold Hysteresis	_	_	8	_	%	
	_	PG Pull-low Voltage	PG sinks 5mA	_	0.25	0.4	V	
— PG Delay Time From $V_{FB} = V_{THPG}$ to rising edge of the V_{PG} 1 2 4 ms	_	PG Debounce Interval	V _{FB} < falling PG voltage threshold	_	10	_	μs	
The state of the s	_	PG Delay Time	From V _{FB} = V _{THPG} to rising edge of the V _{PG}	1	2	4	ms	

Note: 5. Dropout voltage is the voltage difference between the inut and the output at which the output voltage drops 2% below its nominal value.



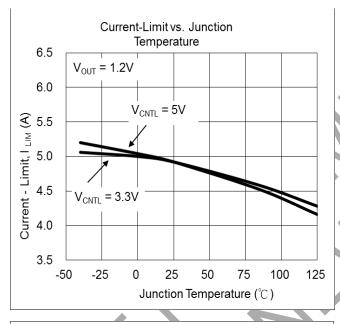
Electrical Characteristics (Cont.)

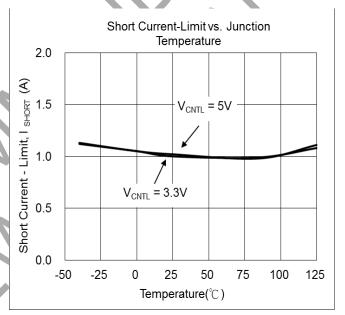
(V_{CNTL} = 5V, V_{IN} = 1.8V, V_{OUT} = 1.2V and T_A = -40 to +85°C, @T_A = +25°C, unless otherwise specified.)

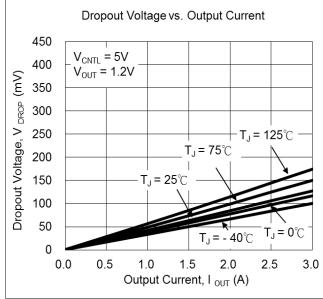
Symbol	Parameter	Test Conditions	AP7175			Unit
Syllibol	Farameter	rest conditions	Min	Тур	Max	Offic
THERMA	THERMAL CHARACTERISTIC					
θ_{JA}	Thermal Resistance Junction-to-Ambient	SO-8EP (Note 6)	_	70		°C/W
θJA	Thermal nesistance Junction-to-Ambient	MSOP-8EP (Note 7)	_	80	_	°C/W
θις Thermal Resistance Junction-to-Case		SO-8EP (Note 6)	_	30		°C/W
θ_{JC}	mermai nesistance junction-to-case	MSOP-8EP (Note 7)		30	_	°C/W

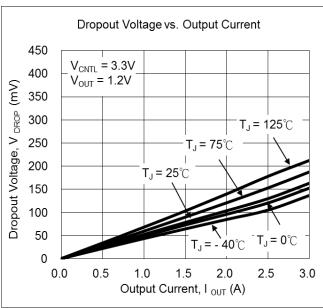
Notes:

Typical Characteristics





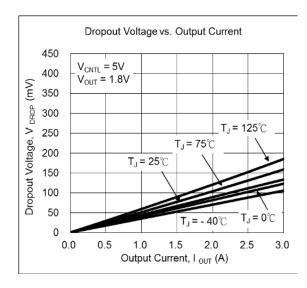


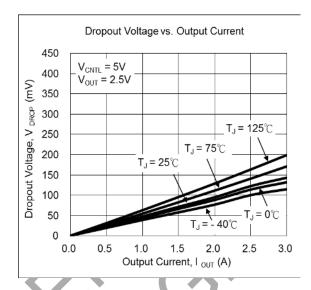


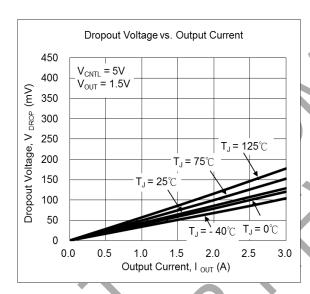
^{6.} Device mounted on 2"*2" FR-4 substrate PC board, 2oz copper, with minimum recommended pad on top layer and thermal vias to bottom layer ground plane.
7. Device mounted on 2"*2" FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

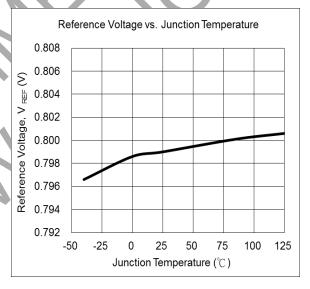


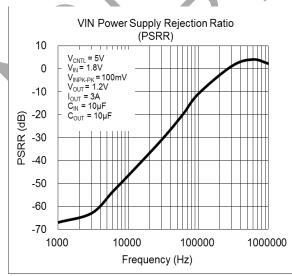
Typical Characteristics (Cont.)

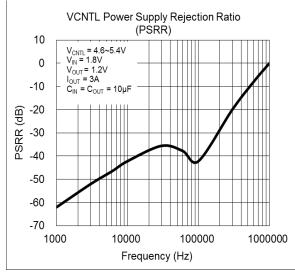






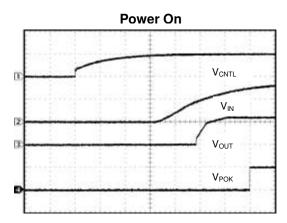








$\textbf{Operating Waveforms} \ (@ \ V_{CNTL} = 5V, \ V_{IN} = 1.8V, \ V_{OUT} = 1.2V, \ T_A = +25^{\circ}C, \ unless \ otherwise \ specified.)$



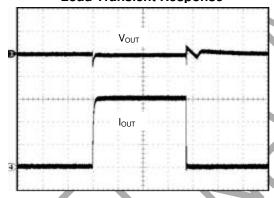
TIME: 2ms/Div

Power Off V_{CNTL} V_{IN} $V_{\text{OUT}} \\$ V_{POK}

 $C_{OUT}{=}10\mu F,\,C_{IN}{=}10\mu F,\,R_L{=}0.4\Omega$

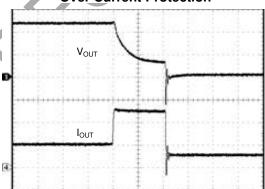
CH1: V_{CNTL}, 5V/Div, DC CH2: V_{IN}, 1V/Div, DC CH3: V_{OUT}, 1V/Div, DC CH4: V_{POK}, 5V/Div, DC TIME: 2ms/Div

Load Transient Response



 l_{OUT} = 10mA to 3A to10mA (rise / fall time =1µs) C_{OUT} = 10µF, C_{IN} = 10µF CH1: V_{OUT} , 50mV/Div, AC CH2: I_{OUT}, 1A/Div, DC TIME: 50µs/Div

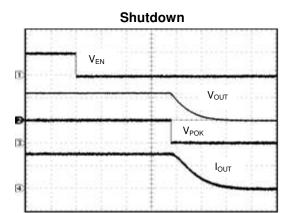
Over Current Protection



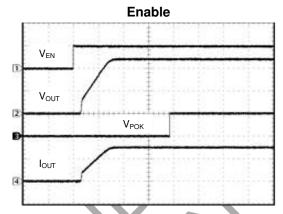
 C_{OUT} = 10 µF, C_{IN} = 10 µF, I_{OUT} = 2A to 5.6A CH1: V_{OUT}, 0.5V/Div, DC CH2: $I_{OUT},$ 2A/Div, DC TIME: 0.2ms/Div



 $\textbf{Operating Waveforms} \ \, \text{(Cont.)} \ \, \text{(@ $V_{CNTL} = 5V$, $V_{IN} = 1.8V$, $V_{OUT} = 1.2V$, $T_{A} = +25^{\circ}C$, unless otherwise specified.)}$



$$\begin{split} &C_{OUT} = 10 \mu F, \ C_{IN} = 10 \mu F, \ R_L = 0.4 \Omega \\ &CH1: \ V_{EN}, \ 5 V/Div, \ DC \\ &CH2: \ V_{OUT}, \ 1 V/Div, \ DC \\ &CH3: \ V_{POK}, \ 5 V/Div, \ DC \\ &CH4: \ I_{OUT}, \ 2 A/Div, \ DC \\ &TIME: \ 4 \mu s/Div \end{split}$$



$$\begin{split} &C_{OUT} = 10 \mu F, \, C_{IN} = 10 \mu F, \, R_L = 0.4 \Omega \\ &CH1: \, V_{EN}, \, 5V/Div, \, DC \\ &CH2: \, V_{OUT}, \, 1V/Div, \, DC \\ &CH3: \, V_{POK}, \, 5V/Div, \, DC \\ &CH4: \, I_{OUT}, \, 2A/Div, \, DC \\ &TIME: \, 1ms/Div \end{split}$$

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AP7175

Application Information

Power Good and Delay

AP7175 monitors the feedback voltage V_{FB} on the FB pin. An internal delay timer is started after the PG voltage threshold (V_{THPG}) on the FB pin is reached. At the end of the delay time an internal NMOS of the PG is turned off to indicate that the power at the output is good (PG). This monitoring function is continued during operation and if V_{FB} falls 8% (typ) below V_{THPG} , the NMOS of the PG is turned on after a delay time of typical 10µs to avoid oscillating of the PG signal.

Power On Reset

AP7175 monitors both supply voltages, V_{CNTL} and V_{IN} to ensure operation as intended. A Soft-Start process is initiated after both voltages exceed their POR threshold during power on. During operation the POR component continues to monitor the supply voltage and pulls the PG low to indicate an out of regulation supply. This function will engage without regard to the status of the output.

Soft-Start

AP7175 incorporates an internal Soft-Start function. The output voltage rise is controlled to limit the current surge during start-up. The typical Soft-Start time is 0.6ms.

Current-Limit Protection

AP7175 monitors the current flow through the NMOS and limits the maximum current to avoid damage to the load and AP7175 during overload conditions.

Short Circuit Current-Limit Protection

AP7175 incorporates a current limit function to reduce the maximum current to 1.1A (typ) when the voltage at FB falls below 0.2V (typ) during an overload or short circuit situation.

During start-up period, this function is disabled to ensure successful heavy load start-up.

Enable Control

If the enable pin (EN) is left open, an internal current source of ~5µA pulls the pin up and enables the AP7175. This will reduce the bill of material saving an external pull up resistor. Driving the enable pin low disables the device. Driving the pin high subsequently initiates a new Soft-Start cycle.

Output Voltage Regulation

Output Voltage is set by resistor divider from V_{QUT} via FB pin to GND. Internally V_{FB} is compared to a 0.8V temperature compensated reference voltage and the NMOS pass element regulates the output voltage while delivering current from V_{IN} to V_{QUT} .

Setting the Output Voltage

A resistor divider connected to FB pin programs the output voltage.

$$V_{OUT} = V_{REF} * \left(1 + \frac{R1}{R2}\right) V$$

R1 is connected from V_{OUT} to FB with Kelvin sensing connection. R2 is connected from FB to GND. To improve load transient response and stability, a bypass capacitor can be connected in parallel with R1. (optional in typical application circuit)

Power Sequencing

AP7175 requires no specific sequencing between V_{IN} and V_{CNTL} . However, care should be taken to avoid forcing V_{OUT} for prolonged time without the presence of V_{IN} . Conduction through internal parasitic diode (from V_{OUT} to V_{IN}) could damage AP7175.

Thermal Shutdown

The PCB layout and power requirements for AP7175 under normal operation condition should allow enough cooling to restrict the junction temperature to +125°C. The packages for AP7175 have an exposed PAD to support this. These packages provide better connection to the PCB and thermal performance. Refer to the layout considerations.

If AP7175 junction temperature reaches +170°C a thermal protection block disables the NMOS pass element and lets the part cool down. After its junction temperature drops by 50°C (typ), a new Soft-Start cycle will be initiated. A new thermal protection will start, if the load or ambient conditions continue to raise the junction temperature to +170°C. This cycle will repeat until normal operation temperature is maintained again.

NOT RECOMMENDED FOR NEW DESIGN - NO ALTERNATE PART



AP7175

Application Information (Cont.)

Output Capacitor

An output capacitor (C_{OUT}) is needed to improve transient response and maintain stability. The ESR (equivalent series resistance) and capacitance drives the selection. Care needs to be taken to cover the entire operating temperature range.

The output capacitor can be an Ultra-Low-ESR ceramic chip capacitor or a low ESR bulk capacitor like a solid tantalum, POSCap or aluminum electrolytic capacitor.

C_{OUT} is used to improve the output stability and reduces the changes of the output voltage during load transitions. The slew rate of the current sensed via the FB pin in AP7175 is reduced. If the application has large load variations, it is recommended to utilize low-ESR bulk capacitors.

It is recommended to place ceramic capacitors as close as possible to the load and the ground pin and care should be taken to reduce the impedance in the layout.

Input Capacitor

To prevent the input voltage from dropping during load steps it is recommended to utilize an input capacitor (C_{IN}) . As with the output capacitor the following are acceptable, Ultra-Low-ESR ceramic chip capacitor or low ESR bulk capacitor like a solid tantalum, POSCap or aluminum electrolytic capacitor. Typically it is recommended to utilize an capacitance of at least $10\mu\text{F}$ to avoid output voltage drop due to reduced input voltage. The value can be lower if V_{IN} changes are not critical for the application.

Layout Considerations

For good ground loop and stability, the input and output capacitors should be located close to the input, output, and ground pins of the device. No other application circuit is connected within the loop. Avoid using vias within ground loop. If vias must be used, multiple vias should be used to reduce via inductance.

The regulator ground pin should be connected to the external circuit ground to reduce voltage drop caused by trace impedance. Ground plane is generally used to reduce trace impedance.

Wide trace should be used for large current paths from VIN to VOUT, and load circuit.

Place the R1, R2, and C1 (optional) near the LDO as close as possible to avoid noise coupling.

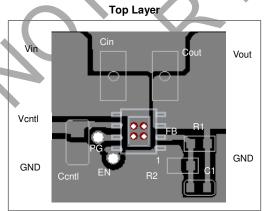
R2 is placed close to device ground. Connect the ground of the R2 to the GND pin by using a dedicated trace.

Connect the pin of the R1 directly to the load for Kelvin sensing.

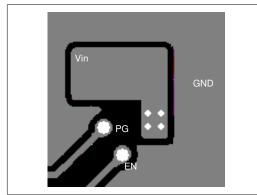
No high current should flow through the ground trace of feedback loop and affect reference voltage stability.

For the packages with exposed pads, heat sinking is accomplished using the heat spreading capability of the PCB and its copper traces. Suitable PCB area on the top layer and thermal vias(0.3mm drill size with 1mm spacing, 4~8 vias at least) to the Vin power plane can help to reduce device temperature greatly.

Reference Layout Plots

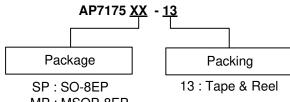


Bottom Layer





Ordering Information

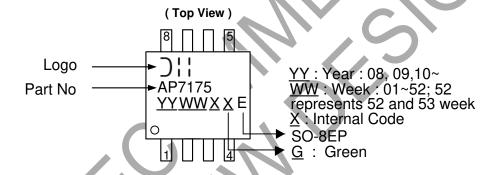


MP: MSOP-8EP

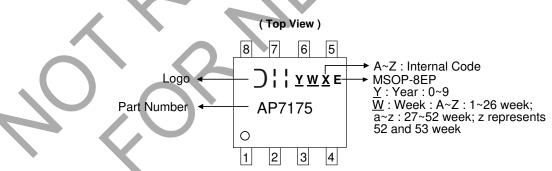
Part Number	Package Code	Dookoaina	13" Tape and Reel		
Part Number	Package Code	Packaging	Quantity	Part Number Suffix	
AP7175SP-13	SP	SO-8EP	2500/Tape & Reel	-13	
AP7175MP-13	MP	MSOP-8EP	2500/Tape & Reel	-13	

Marking Information

(1) SO-8EP



(2) MSOP-8EP

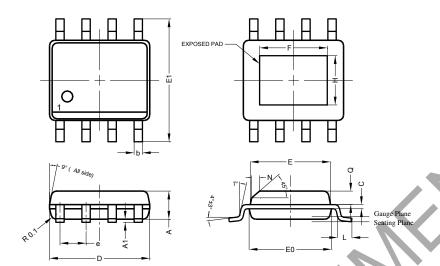




Package Outline Dimensions

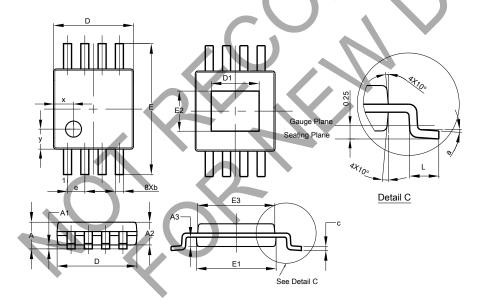
Please see http://www.diodes.com/package-outlines.html for the latest version.

(1) SO-8EP



	SO-8EP				
Dim	Min	Max	Тур		
Α	1.40	1.50	1.45		
A 1	0.00	0.13	1		
b	0.30	0.50	0.40		
С	0.15	0.25	0.20		
D	4.85	4.95	4.90		
E	3.80	3.90	3.85		
E0	3.85	3.95	3.90		
E1	5.90	6.10	6.00		
е	1	1	1.27		
F	2.75	3.35	3.05		
H	2.11	2.71	2.41		
Ľ	0.62	0.82	0.72		
N	-	-	0.35		
Q	0.60	0.70	0.65		
All Di	All Dimensions in mm				

(2) MSOP-8EP



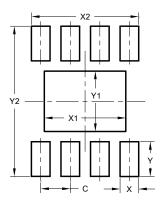
MSOP-8EP					
Dim	Min	Max	Тур		
Α	-	1.10	-		
A1	0.05	0.15	0.10		
A2	0.75	0.95	0.86		
A3	0.29	0.49	0.39		
b	0.22	0.38	0.30		
С	0.08	0.23	0.15		
D	2.90	3.10	3.00		
D1	1.60	2.00	1.80		
Е	4.70	5.10	4.90		
E1	2.90	3.10	3.00		
E2	1.30	1.70	1.50		
E3	2.85	3.05	2.95		
е	-	-	0.65		
L	0.40	0.80	0.60		
а	0°	8°	4°		
Х	-	-	0.750		
у	-	-	0.750		
All Dimensions in mm					



Suggested Pad Layout

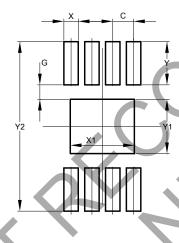
Please see http://www.diodes.com/package-outlines.html for the latest version.

(1) SO-8EP



Dimensions	Value (in mm)
С	1.270
X	0.802
X1	3.502
X2	4.612
Υ	1.505
Y1	2.613
Y2	6.500

(2) MSOP-8EP



Dimensions	Value (in mm)	
С	0.650	
G	0.450	
X	0.450	
X1	2.000	
Υ	1.350	
Y1	1.700	
Y2	5.300	

NOT RECOMMENDED FOR NEW DESIGN -NO ALTERNATE PART



AP7175

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